

20 V, 4.1 A P-channel Trench MOSFET Rev. 1 — 21 April 2011

Product data sheet

Product profile 1.

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low R_{DSon}
- Very fast switching

1.3 Applications

- Relay driver
- High-speed line driver

- Trench MOSFET technology
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C	<u>[1]</u>	-	-	-4.1	А
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I _D = -2.4 A; T _j = 25 °C		-	48	55	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

Pinning information 2.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		2
2	D	drain		
3	G	gate	0	
4	S	source		Ĵ LI
5	D	drain	SOT457 (TSOP6)	Ś
6	D	drain		017aaa094



3. Ordering information

Table 3. Orderin	g information		
Type number	Package		
	Name	Description	Version
PMN48XP	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 4.Marking codes

Type number	Marking code
PMN48XP	ZV

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C	<u>[1]</u>	-	-4.1	А
		V_{GS} = -4.5 V; T_{amb} = 100 °C	<u>[1]</u>	-	-2.5	А
I _{DM}	peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \mu\text{s}$		-	-20	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	530	mW
			<u>[1]</u>	-	1285	mW
		T _{sp} = 25 °C		-	6250	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode					
I _S	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-1.4	А

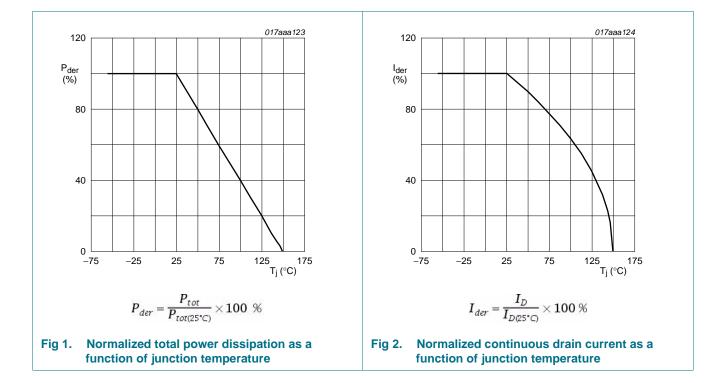
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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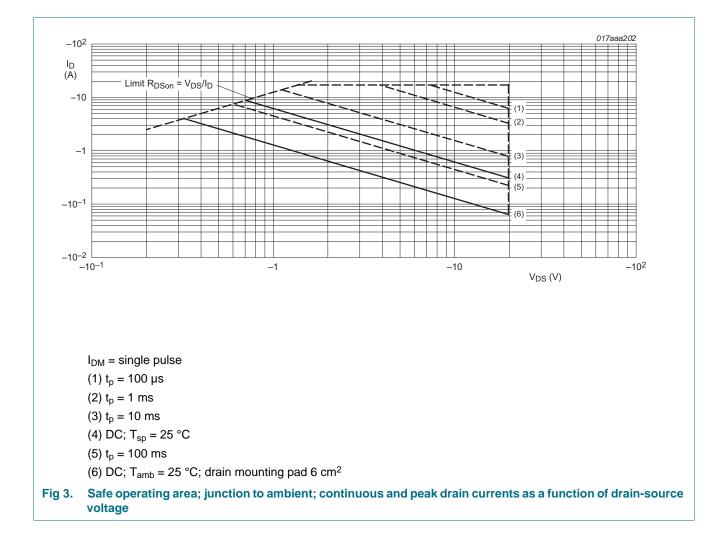
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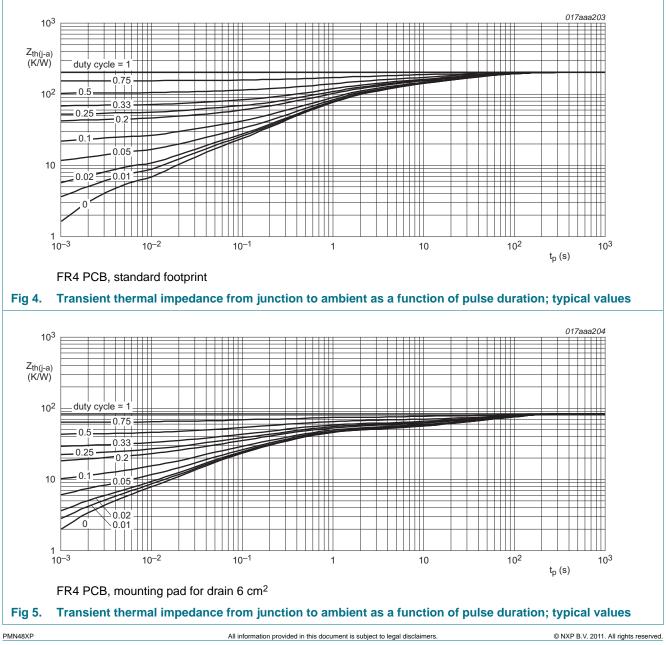
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6. Thermal characteristics

Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	<u>[1]</u>	-	204	235	K/W
	from junction to ambient		[2]	-	84	97	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	17	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

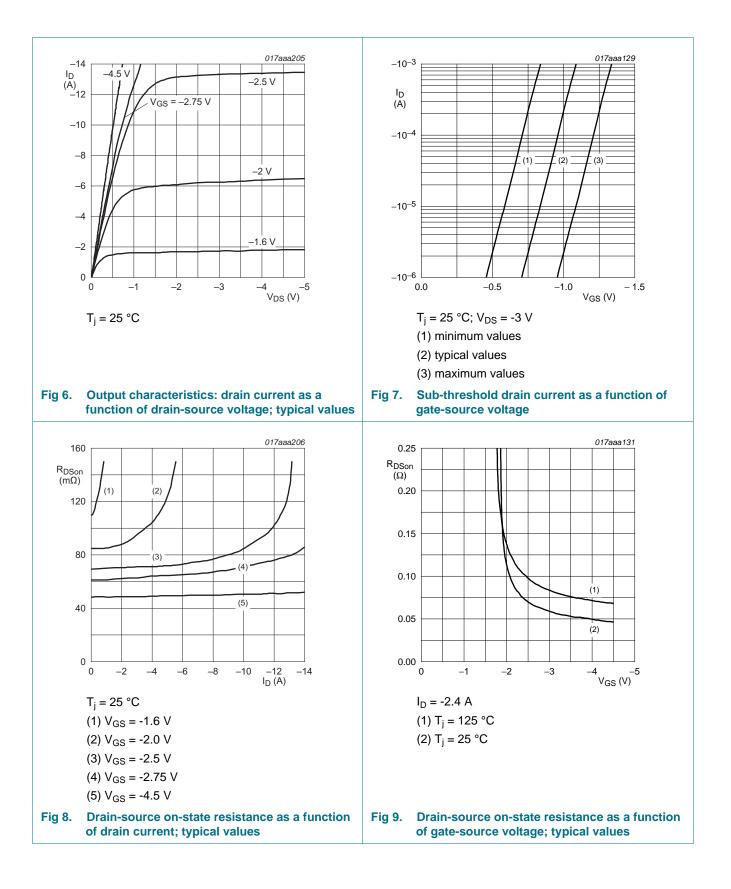


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7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-0.75	-1	-1.25	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	-	-1	μA
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μA
I _{GSS}	gate leakage current	V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-100	nA
R_{DSon}	drain-source on-state	V_{GS} = -4.5 V; I _D = -2.4 A; T _j = 25 °C	-	48	55	mΩ
I	resistance	V_{GS} = -4.5 V; I _D = -2.4 A; T _j = 150 °C	-	70	80	mΩ
		V_{GS} = -2.5 V; I _D = -2 A; T _j = 25 °C	-	72	82	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -5 \text{ V}; \text{ I}_{D} = -2.4 \text{ A}; \text{ T}_{j} = 25 \text{ °C}$	-	10	-	S
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = -1 \text{ A}; V_{DS} = -10 \text{ V}; V_{GS} = -4.5 \text{ V};$	-	8.7	13	nC
Q_{GS}	gate-source charge	$T_j = 25 \ ^{\circ}C$	-	1.8	-	nC
Q_{GD}	gate-drain charge		-	1.7	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = -10 V; f = 1 MHz;$	-	1000	-	pF
C _{oss}	output capacitance	$T_j = 25 \ ^{\circ}C$	-	130	-	pF
C _{rss}	reverse transfer capacitance		-	90	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -10 \text{ V}; V_{GS} = -5 \text{ V}; \text{R}_{G(ext)} = 6 \Omega;$	-	15	-	ns
t _r	rise time	T _j = 25 °C; I _D = -1 A	-	22	-	ns
t _{d(off)}	turn-off delay time		-	51	-	ns
t _f	fall time		-	22	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	I _S = -2.4 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.75	-1	V

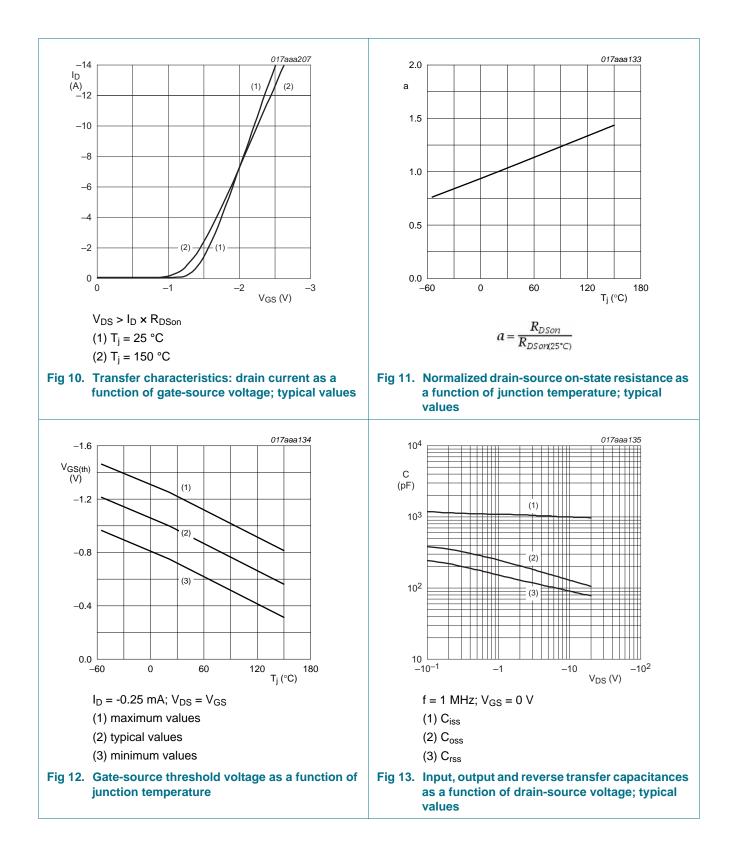
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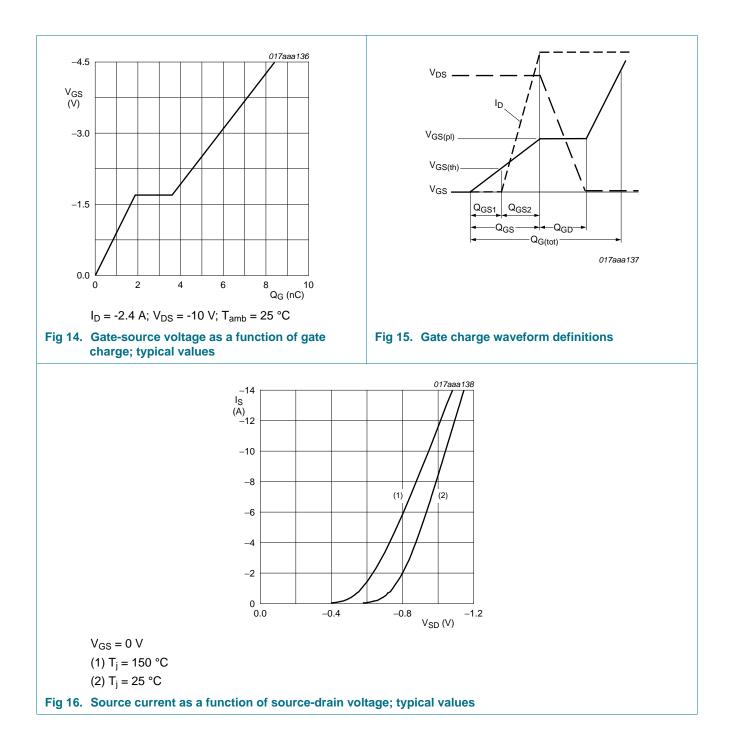
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8. Package outline

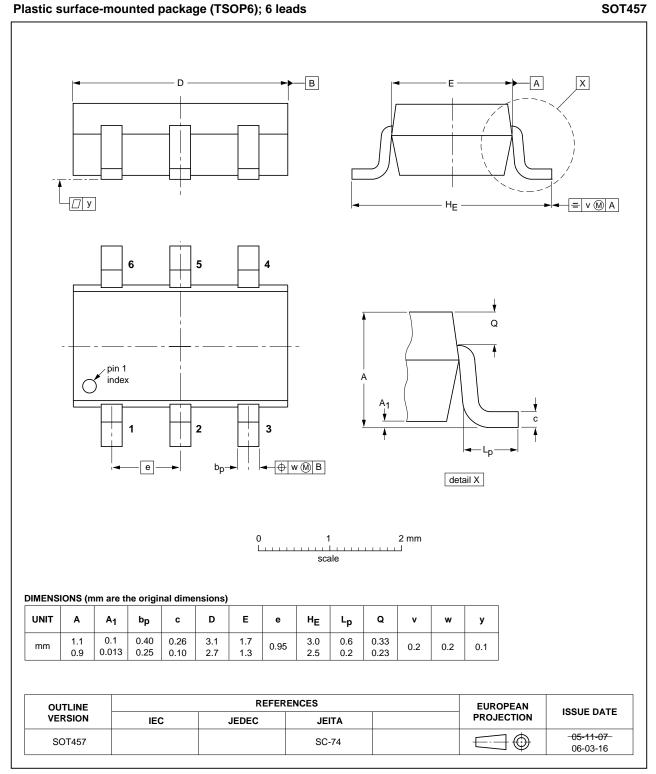
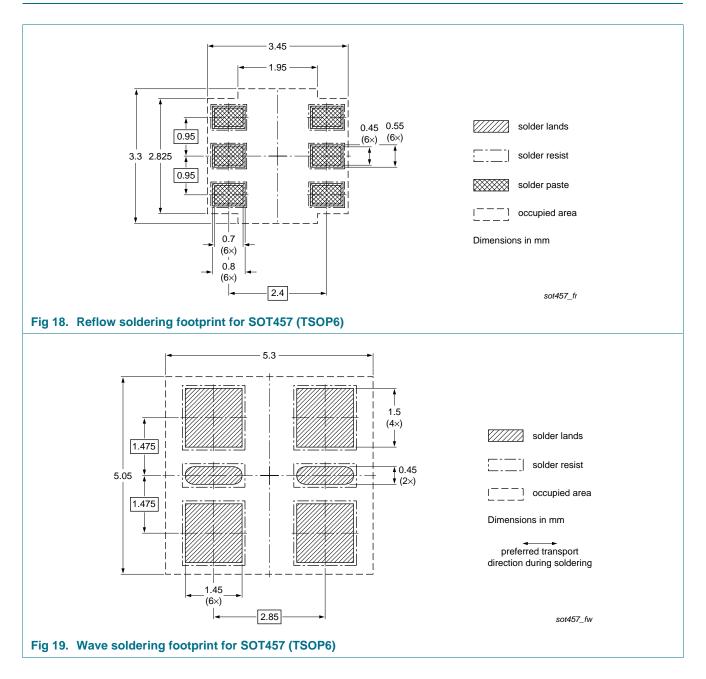


Fig 17. Package outline SOT457 (TSOP6)

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9. Soldering



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10. Revision history

Table 8.	Revision history						
Document	ID	Release date	Data sheet status	Change notice	Supersedes		
PMN48XP	v.1	20110421	Product data sheet	-	-		

11. Legal information

11.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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